

ABSTRACT:

The invention relates to a thin film capacitor with a carrier substrate (1), at least two interdigitated electrodes (4, 5), and a dielectric (3). A staggered arrangement of at least one interdigitated electrode (4) below the dielectric (3) with respect to an interdigitated electrode (5) above the dielectric (3) results in a breakdown-resistant thin film capacitor which

5 can be manufactured in the same production process as a standard monolayer capacitor.

Fig. 1

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